

2/IDS
11/3/01
R. Walker

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Rule 53(b) Divisional Application of:

Nobuhiko HAYASHI, et al.

Divisional of S.N.: 09/361,246 Filed July 27, 1999

Group Art Unit: To Be Assigned

Filed: Herewith

Examiner: To Be Assigned

For: SEMICONDUCTOR DEVICE AND METHOD OF FABRICATING THE SAME AND
METHOD OF FORMING NITRIDE BASED SEMICONDUCTOR LAYER



INFORMATION DISCLOSURE STATEMENT
PURSUANT TO 37 CFR 1.97(b)

Commissioner for Patents
Washington, D.C. 20231

September 19, 2001

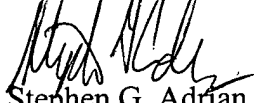
Sir:

This Information Disclosure Statement is being filed in order to comply with Applicant's duty of disclosure under 37 CFR 1.56. The documents listed on the Form PTO-1449 were made of record in parent application Serial No. 09/361,246 filed July 27, 1999.

The Commissioner is authorized to charge our Deposit Account No. 01-2340 for any fee which is deemed by the Patent and Trademark Office to be required to effect consideration of this statement.

Respectfully submitted,

ARMSTRONG, WESTERMAN, HATTORI,
MCLELAND & NAUGHTON, LLP


Stephen G. Adrian
Attorney for Applicants
Registration No. 32,878

Attorney Docket No. 990852A
1725 K Street, N.W., Suite 1000
Washington, D.C. 20006
Tel: (202) 659-2930
Fax: (202) 887-0357
Enclosures: PTO-1449
Q:\FLOATERS\SGA\011204 IDS-DIV.wpd